



IRFU2905Z Information



For Reference Only

Part Number IRFU2905Z

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 55V 42A I-PAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRFU2905Z Specifications

Manufacturer Part Number IRFU2905Z Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 42A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 44nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1380pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 110W (Tc) Rds On (Max) @ Id, Vgs 14.5 mOhm @ 36A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA		
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Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) Input Capacitance (Max) 110W (Tc) Rds On (Max) @ Id, Vgs 14.5 mOhm @ 36A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Current - Continuous Drain (Id) @ 25°C	42A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1380pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14.5 mOhm @ 36A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14.5 mOhm @ 36A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ± 20 VFET Feature-Power Dissipation (Max) 110 W (Tc)Rds On (Max) @ Id, Vgs 14.5 mOhm @ 36 A, 10 VOperating Temperature -55° C $\sim 175^{\circ}$ C (TJ)Mounting TypeThrough HoleSupplier Device PackageIPAK (TO-251)Package / CaseTO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	44nC @ 10V
FET Feature - Power Dissipation (Max) 110W (Tc) Rds On (Max) @ Id, Vgs 14.5 mOhm @ 36A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	1380pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14.5 mOhm @ 36A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs14.5 mOhm @ 36A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageIPAK (TO-251)Package / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	110W (Tc)
Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	14.5 mOhm @ 36A, 10V
Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	IPAK (TO-251)
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

IRFU2905Z Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFU2905Z Payment Methods



















IRFU2905Z Shipping Methods













If you have any question about IRFU2905Z, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com